

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	16	yang near nian.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 17:54	
2	BRS	L2	27	wang near zhigang.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:03	
3	BRS	L3	54	(floating near gate near flash near memory).ti.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:07	
4	BRS	L4	580	floating near gate near flash near memory	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	4	(floating near gate near flash near memory) near25 (barrier)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:10	
6	BRS	L6	108	(floating near gate near3 electrode) near25 (barrier)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:10	
7	BRS	L7	1	(floating near gate near3 electrode) near25 (barrier) near15 (hard near mask)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:11	
8	BRS	L8	27115	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	27061	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 (sidewall\$1 or side near wall\$1)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:12	
10	BRS	L10	27022	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 (sidewall\$1 or side near wall\$1), near15 (channel)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:13	
11	BRS	L11	27022	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 (sidewall\$1 or side near wall\$1) near15 (channel) near15 (tunnel near dielectric)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:15	
12	BRS	L12	27059	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 (sidewall\$1) or (side near wall\$1) near15 (channel) near15 (tunnel near dielectric)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:16	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	27059	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 ((sidewall\$1) or (side near wall\$1) near15 (channel) near15 (reverse near tunnel near dielectric)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:16	
14	BRS	L14	27022	(floating near gate) or (electrode) near25 (barrier) near15 (hard near mask) near15 ((sidewall\$1) or (side near wall\$1)) near15 (channel) near15 (reverse near tunnel near dielectric)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:17	
15	BRS	L15	1	((floating near gate) or (electrode)) near25 (barrier) near15 (hard near mask) near15 ((sidewall\$1) or (side near wall\$1)) near15 (channel) near15 (reverse near tunnel near dielectric)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:17	
16	BRS	L16	40	((floating near gate) or (electrode)) near25 (barrier) near15 (hard near mask) near15 ((sidewall\$1) or (side near wall\$1))	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:24	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
17	BRS	L17	677	((floating near gate) or (electrode)) near25 (barrier) near15 ((sidewall\$1) or (side near wall\$1))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:25	
18	BRS	L18	30	((floating near gate) or (electrode)) near25 (barrier) near15 ((sidewall\$1) or (side near wall\$1)) near15 (channel)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:31	
19	BRS	L19	52	((floating near gate) or (electrode)) near25 (barrier) near15 ((sidewall\$1) or (side near wall\$1) or (spacer\$1)) near15 (channel)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:35	
20	BRS	L20	3165	((floating near gate) or (electrode)) near25 ((sidewall\$1) or (side near wall\$1) or (spacer\$1)) near15 (channel)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 18:36	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	1235	((floating near gate) or (electrode)) near25 ((sidewall\$1) or (side near wall\$1) or (spacer\$1)) near15 (channel) near25 ((tunnel) or (insulat\$3 or dielectric))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 19:09	
22	BRS	L22	99	((floating near gate) or (electrode)) near25 ((sidewall\$1) or (side near wall\$1) or (spacer\$1)) near15 (channel) near25 ((tunnel) or (insulat\$3 or dielectric)) near25 (control near gate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/04/1 2 19:09	

	U	I	Document ID	Title	Current OR	Pages	Issue Date
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030216042 A1	CMP slurry for oxide film and method of forming semiconductor device using the same	438/689	12	20031120
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6660588 B1	High density floating gate flash memory and fabrication processes therefor	438/257	25	20031209
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6617639 B1	Use of high-K dielectric material for ONO and tunnel oxide to improve floating gate flash memory coupling	257/324	14	20030909
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6274418 B1	Method of manufacturing flash memory cell	438/211	4	20010814